

ABSTRACT OF THE DISCLOSURE

A semiconductor device includes a SiC substrate and an ohmic electrode, a semiconductor member including a SiC member and a SiGe member being formed between the SiC substrate and the ohmic electrode,
5 wherein the semiconductor member is composed of a SiGe member formed on a SiC member, and the ohmic electrode is formed on the SiGe member, whereby the ohmic electrode with a low resistance can be formed on the SiC substrate without conducting a heat treatment at a high temperature.